

DESCRIPTION

The MX3409 uses advanced trench technology to provide excellent $R_{DS(ON)}$. This device is suitable for use as a load switch or in PWM applications.

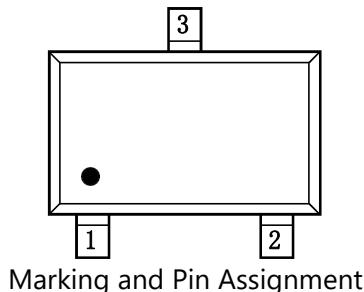
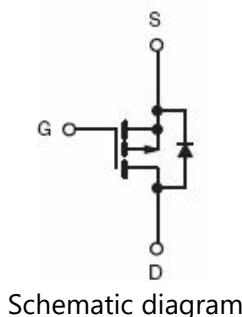
GENERAL FEATURES

- $V_{DS} = -30V$, $I_D = -4.3A$
 $R_{DS(ON)}(\text{Typ.}) = 60\text{m}\Omega$ @ $V_{GS} = -4.5V$
 $R_{DS(ON)}(\text{Typ.}) = 38\text{m}\Omega$ @ $V_{GS} = -10V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

APPLICATION

- PWM applications
- Load switch
- Power management

PINOUT



ORDERING INFORMATION

Part Number	Marking	Storage Temperature	Package	Devices Per Reel
MX3409		-55°C to 150°C	SOT-23-3	3000

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-4.3	A
Drain Current-Pulsed ^(Note1)	I_{DM}	-20	A
Drain-Source Diode Forward Current	I_S	-1.25	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction Temperature Range	T_J	-55 to 150	°C

Note 1. Repetitive Rating: Pulse width limited by maximum junction temperature.


ELECTRICAL CHARACTERISTICS($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA

On Characteristics^(Note3)

Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.4	-1.6	-2.4	V
		$V_{GS}=-4.5V, I_D=-4A$	-	60	100	$m\Omega$
		$V_{GS}=-10V, I_D=-4.3A$	-	38	50	$m\Omega$
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-4.1A$	5.5	-	-	S

Dynamic Characteristics^(Note4)

Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V, F=1.0MHz$	-	700	-	pF
Output Capacitance	C_{oss}		-	120	-	pF
Reverse Transfer Capacitance	C_{rss}		-	75	-	pF

Switching Characteristics^(Note4)

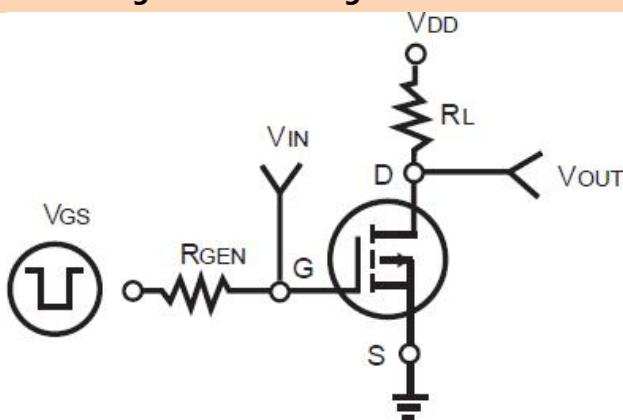
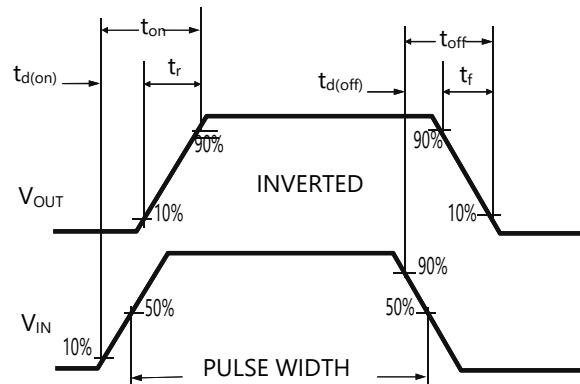
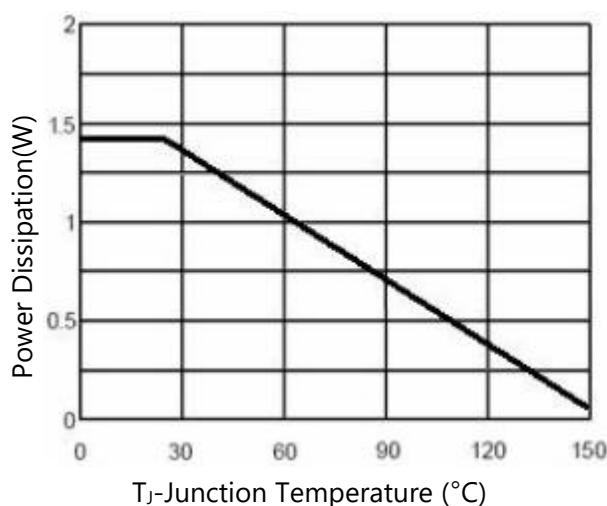
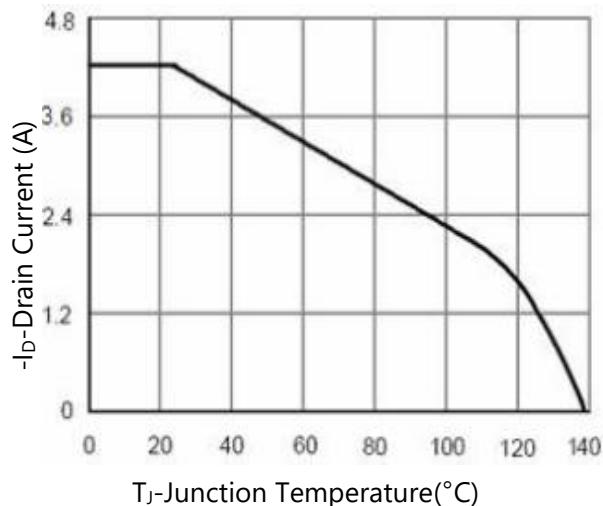
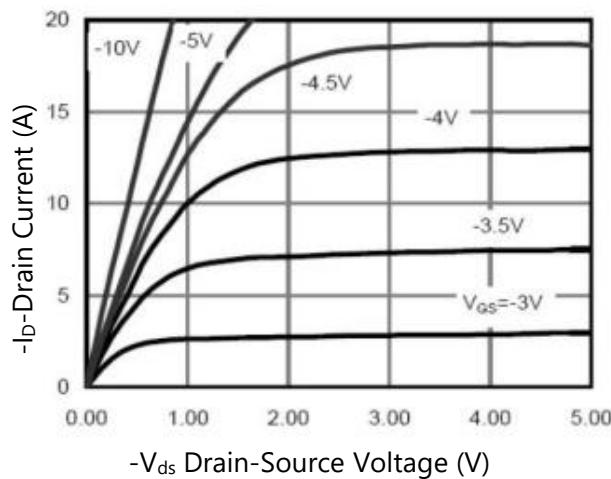
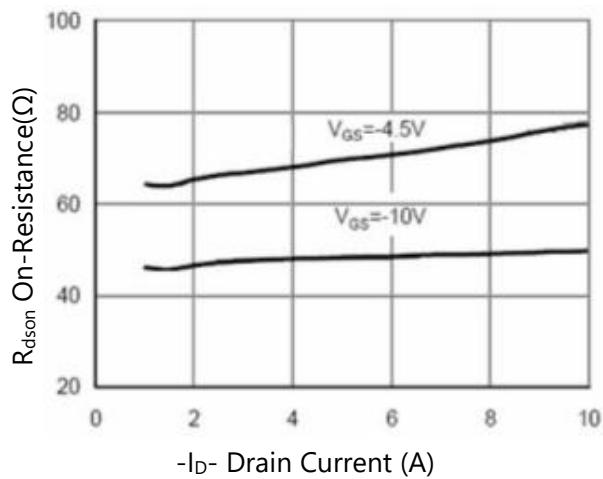
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-15V, RL=3.6\Omega, V_{GS}=-10V, R_{GEN}=3\Omega$	-	9	-	nS
Turn-on Rise Time	t_r		-	5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	28	-	nS
Turn-Off Fall Time	t_f		-	13.5	-	nS
Total Gate Charge	Q_g	$V_{DS}=-15V, I_D=-4.2A, V_{GS}=-4.5V$	-	14	-	nC
Gate-Source Charge	Q_{gs}		-	3.1	-	nC
Gate-Drain Charge	Q_{gd}		-	3	-	nC

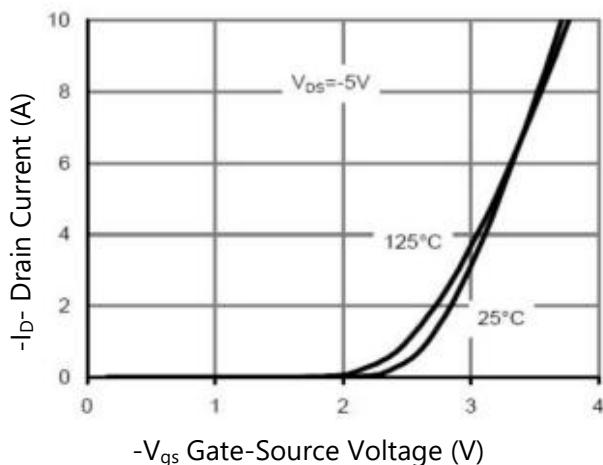
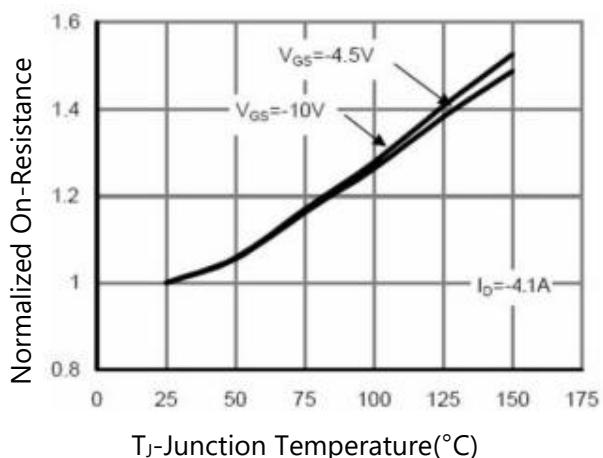
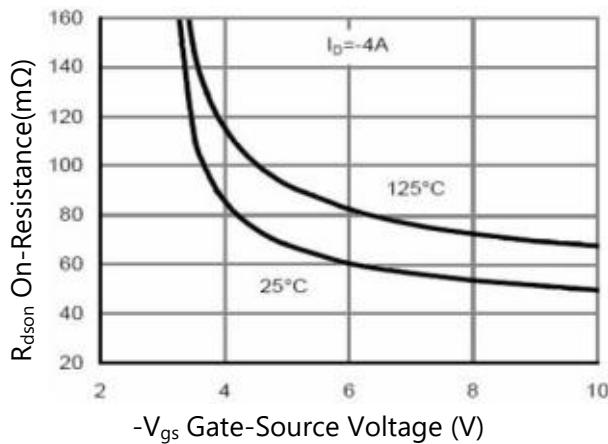
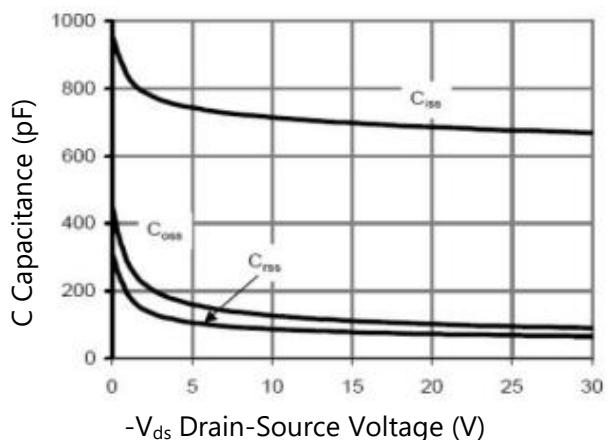
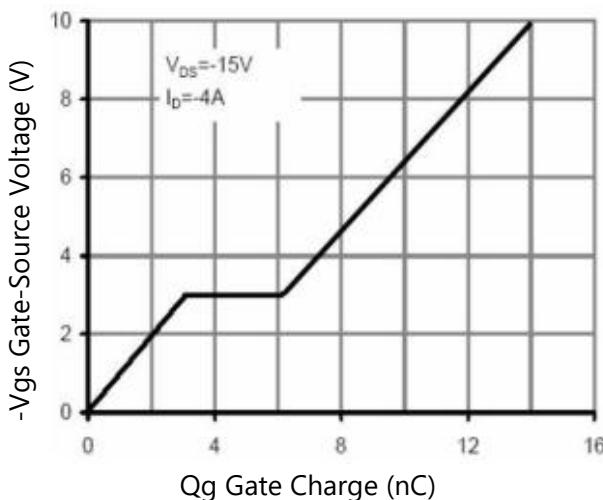
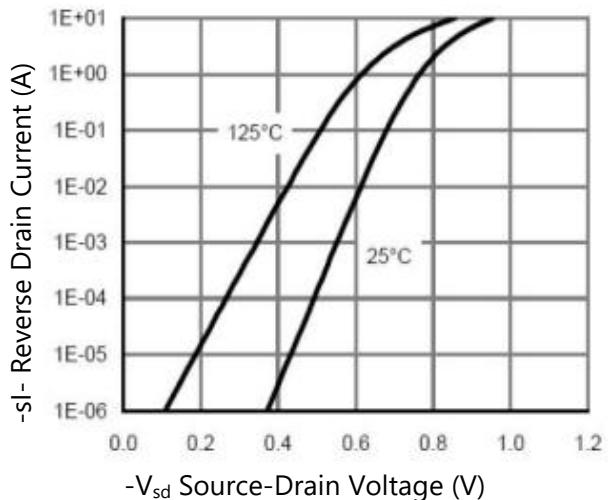
Drain-Source Diode Characteristics

Diode Forward Voltage ^(Note3)	V_{SD}	$V_{GS}=0V, I_S=-4.2A$	-	-	-1.2	V
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Note 3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

Note 4. Guaranteed by design, not subject to production


TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 1. Switching Test Circuit

Figure 2. Switching Waveform

Figure 3. Power Dissipation

Figure 4. Drain Current

Figure 5. Output Characteristics

Figure 6. Drain-Source On-Resistance



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 7. Transfer Characteristics

Figure 8. Drain-Source On-Resistance

Figure 9. $R_{ds(on)}$ vs V_{gs}

Figure 10. Capacitance vs V_{ds}

Figure 11. Gate Charge

Figure 12. Source- Drain Diode Forward


TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 11. Safe Operation Area

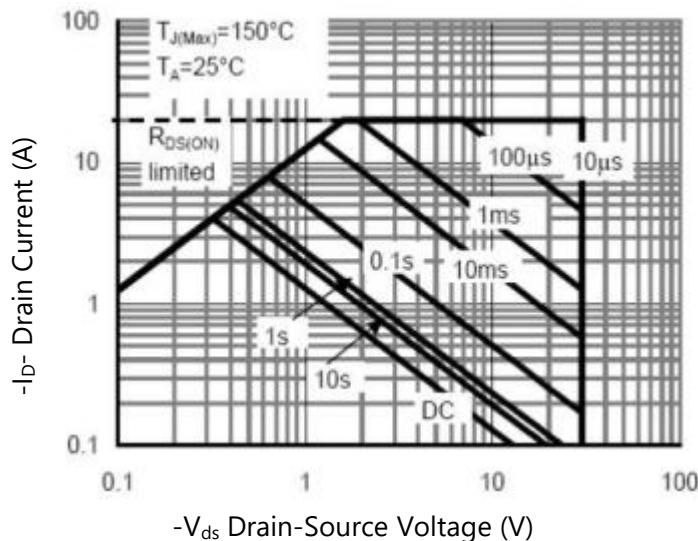
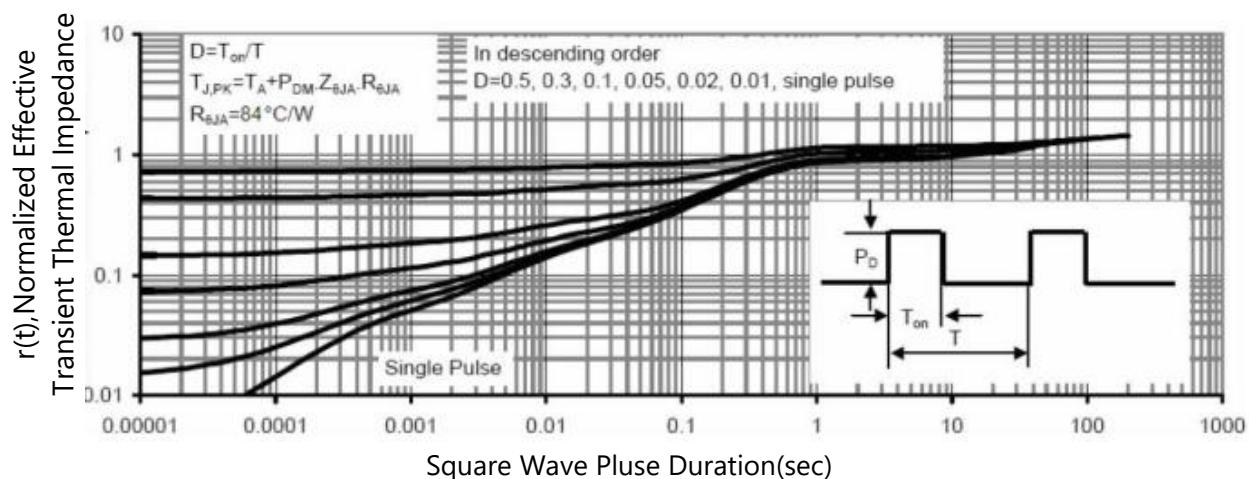
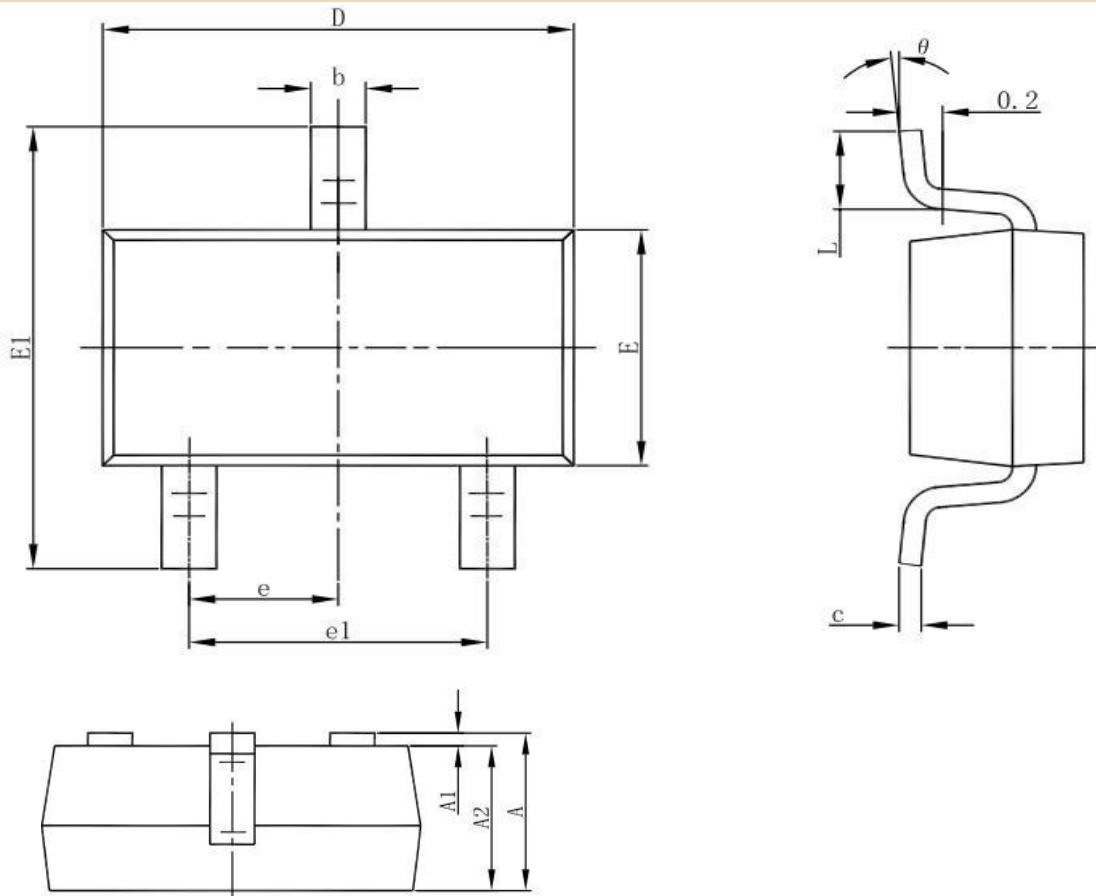


Figure 12. Normalized Maximum Transient Thermal Impedance



PACKAGE INFORMATION

SOT23-3L


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°